

Vishay Siliconix

# Dual P-Channel 1.8-V (G-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	<b>R<sub>DS(on)</sub> (</b> Ω <b>)</b>	I <sub>D</sub> (A)		
	0.021 at V <sub>GS</sub> = - 4.5 V	- 8.0		
- 8	0.027 at V <sub>GS</sub> = - 2.5 V	- 7.0		
	0.040 at V <sub>GS</sub> = - 1.8 V	- 5.8		

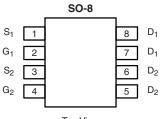
#### **FEATURES**

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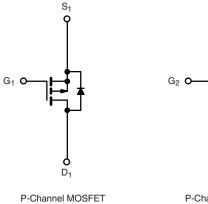
- Halogen-free According to IEC 61249-2-21
  Definition
  - TrenchFET<sup>®</sup> Power MOSFETs: 1.8 V Rated
- Compliant to RoHS Directive 2002/95/EC



FREE Available



Top View



P-Channel MOSFET

 $D_2$ 

 $S_2$ 

Q

Ordering Information: Si4965DY-T1-E3 (Lead (Pb)-free)
Si4965DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

<b>ABSOLUTE MAXIMUM RATINGS</b> T	A = 25 °C, unle	ss otherwise n	oted		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	- 8	M	
Gate-Source Voltage		V <sub>GS</sub>	± 8	V	
	T <sub>A</sub> = 25 °C	– I <sub>D</sub>	- 8.0		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a, b</sup>	T <sub>A</sub> = 70 °C		- 6.4		
Pulsed Drain Current		I <sub>DM</sub>	- 30	A	
Continuous Source Current (Diode Conduction) <sup>a, b</sup>		۱ <sub>S</sub>	- 1.7		
······································	T <sub>A</sub> = 25 °C	PD	2.0	W	
Maximum Power Dissipation <sup>a, b</sup>	T <sub>A</sub> = 70 °C	'D	1.3		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 10 s	- R <sub>thJA</sub>		62.5	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		93		C/W

Notes:

a. Surface Mounted on FR4 board.

b.  $t \leq 10$  s.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \ \mu A$	- 0.45			۷	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V},  V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -8 V, V_{GS} = 0 V$			- 1		
		$V_{DS}$ = - 8 V, $V_{GS}$ = 0 V, $T_{J}$ = 70 °C		- 5	μA		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge$ - 5 V, $V_{GS}$ = - 4.5 V	- 20			А	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -8.0 \text{ A}$		0.0175	0.021	Ω	
		$V_{GS}$ = - 2.5 V, I <sub>D</sub> = - 7.0 A		0.022	0.027		
		$V_{GS}$ = - 1.8 V, I <sub>D</sub> = - 5.8 A		0.031	0.040		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = -5 V, I_{D} = -8.0 A$		27		S	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = - 1.7 A, V <sub>GS</sub> = 0 V			- 1.2	V	
Dynamic <sup>b</sup>			•	•			
Total Gate Charge	Qg			36	55	nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = - 4 V, $V_{GS}$ = - 4.5 V, $I_{D}$ = - 8.0 A		7.5			
Gate-Drain Charge	Q <sub>gd</sub>			5.0			
Turn-On Delay Time	t <sub>d(on)</sub>			35	70		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 4 V, $R_L$ = 4 $\Omega$		45	90		
Turn-Off Delay Time	t <sub>d(off)</sub>	$\text{I}_{\text{D}}\cong$ - 1 A, $\text{V}_{\text{GEN}}$ = - 4.5 V, $\text{R}_{\text{g}}$ = 6 $\Omega$		170	340	ns	
Fall Time	t <sub>f</sub>			90	180		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 1.7 A, dl/dt = 100 A/μs		60	90		

Notes:

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

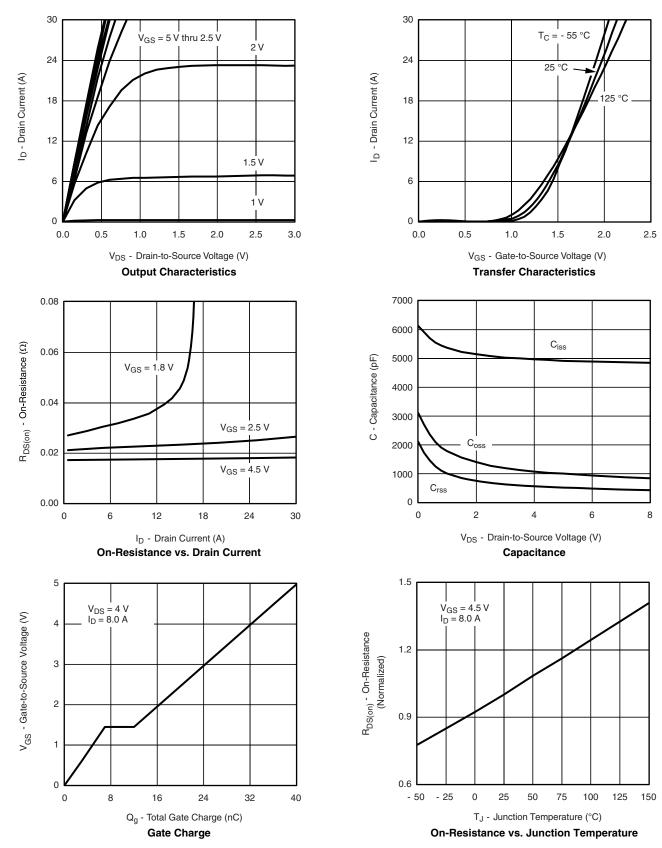
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



### Si4965DY Vishay Siliconix

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

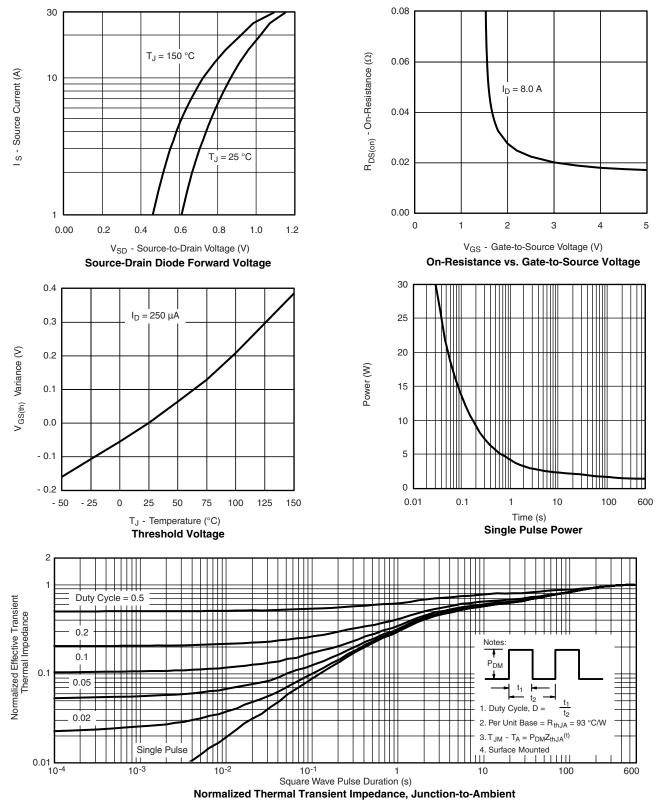


## Si4965DY

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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?70826">www.vishay.com/ppg?70826</a>.



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